

产品规格书

Specifcation of products

产品名称: 整流单管模块

产品型号: MD600A-Y12

浙江世菱半导体有限公司
ZHEJIANG SHILING SEMICONDUCTOR CO., LTD.

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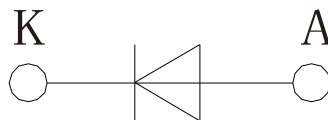
Http://www.smrshiling.com

拟制	审核	核准
林益龙	曹剑龙	宗瑞

SYMBOL	CHARACTERISTIC	TEST CONDITIONS	T _j (°C)	VALUE			UNIT
				Min	Type	Max	
I _{F(AV)}	Mean forward current	180° half sine wave 50Hz Single side cooled, T _C = 100°C	150			600	A
I _{F(RMS)}	RMS forward current	Single side cooled, T _C = 100°C	150			942	A
V _{RRM}	Repetitive peak reverse voltage	V _{RRM} tp=10ms V _{RSM} = V _{DRM} & V _{RRM} + 200V	150	600		2200	V
I _{RRM}	Repetitive peak current	at V _{RRM}	150			15	mA
I _{FSM}	Surge forward current	10ms half sine wave V _R = 0.6V _{RRM}	150			18	KA
I ² t I	² T for fusing coordination					1805	A ² s*10 ³
V _{FO}	Threshold voltage		150			0.75	V
r _F	Forward slope resistance						0.25
V _{FM}	Peak forward voltage	I _{FM} = 3000A	25			1.5	V
R _{th(j-c)}	Thermal resistance Junction to heatsink	At 180° sine Single side cooled				0.070	°C/W
V _{iso}	Isolation voltage	50Hz, RM. S, t=1min, I _{iso} : 1mA (max)		3000			V
F _m	Terminal connection torque(M6)				5.0		N.m
	Mounting torque(M10)				9.0		N.m
T _{stg}	Stored temperature			-40		125	°C
W _t	Weight				900		g
Outline							

OUTLINE DRAWING & CIRCUIT DIAGRAM

MD



Rating and Characteristic

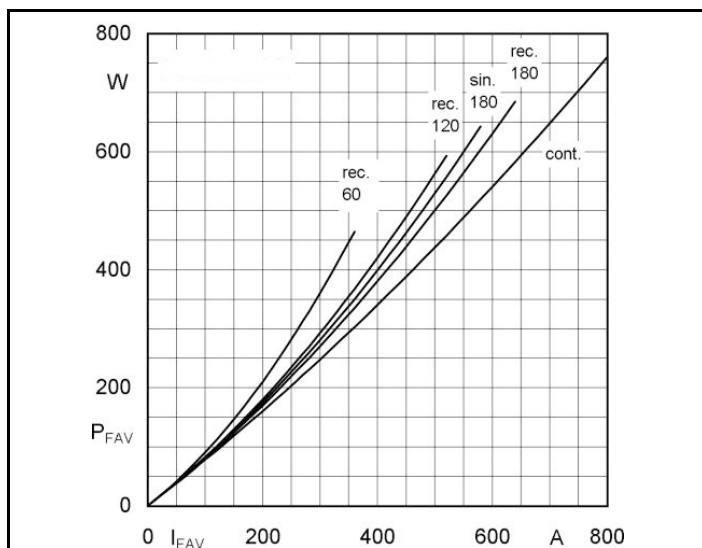


Fig.11L Power dissipation per diode vs. forward current

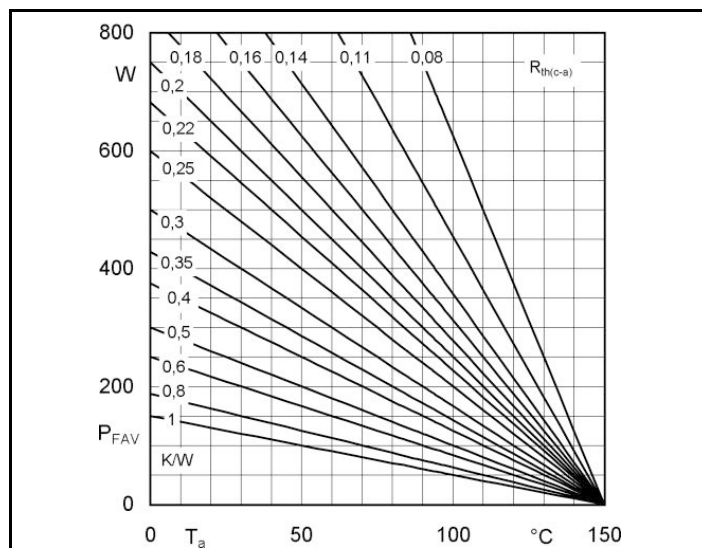


Fig.11R Power dissipation per diode vs. ambient temperature

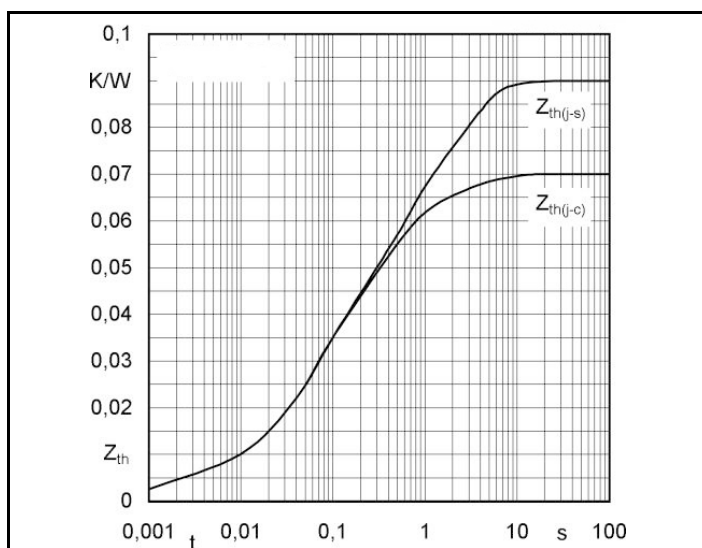


Fig.14 Transient thermal impedance vs. time

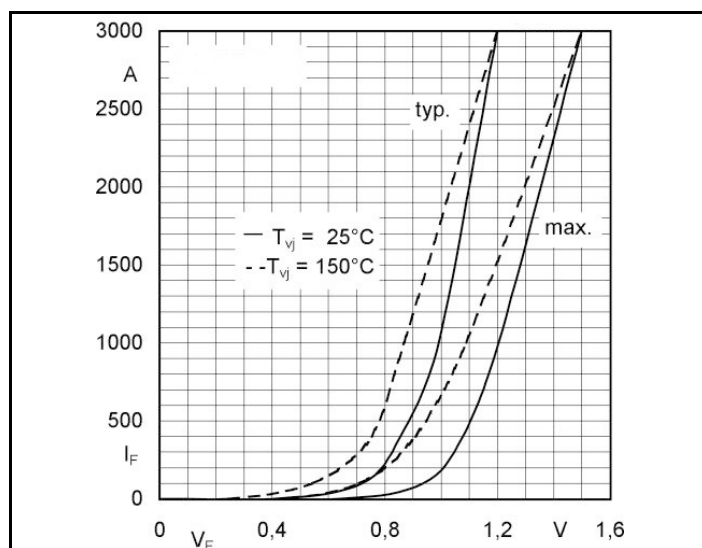


Fig.15 Forward characteristics

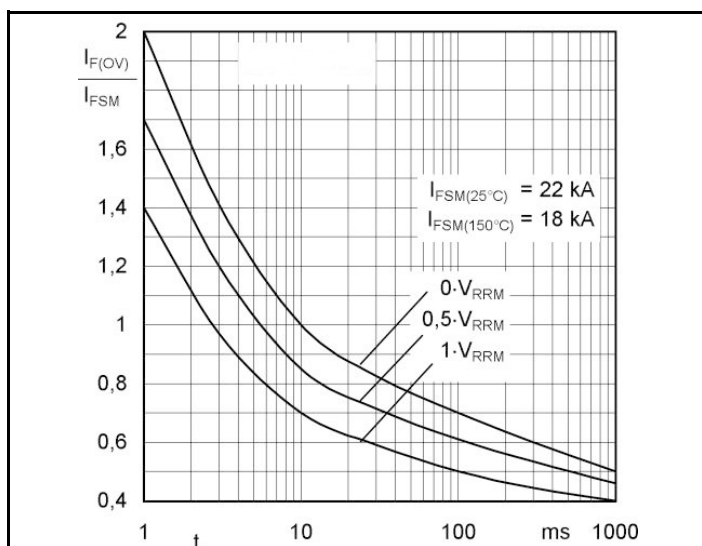


Fig.16 Surge overload current vs. time

Outside Dimension

